

ABSTRACT

SILICON WAFER POLISHING METHOD AND SILICON WAFER

This invention is to provide a method of polishing a silicon wafer wherein a high flatness can be attained likewise the conventional polishing method and further the occurrence of defects due to the remaining of substances included in the polishing solution on the surface of the wafer can be suppressed as well as a polished silicon wafer.

The method of polishing a silicon wafer by supplying a polishing solution containing abrasive grains onto a surface of a polishing pad and then relatively sliding the polishing pad to a silicon wafer to polish the surface of the silicon wafer, is characterized in that the number of abrasive grains included in the polishing solution is controlled to not more than  $5 \times 10^{13}$  grains/cm<sup>3</sup>.

Figure 3